

isc Silicon NPN Power Transistors

TIP29C

DESCRIPTION

- Collector-Emitter Sustaining Voltage-
: $V_{CEO(SUS)} = 100V(\text{Min})$
- Collector-Emitter Saturation Voltage-
: $V_{CE(sat)} = 0.7V(\text{Max.}) @ I_C = 1.0A$
- Complement to Type TIP30C
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

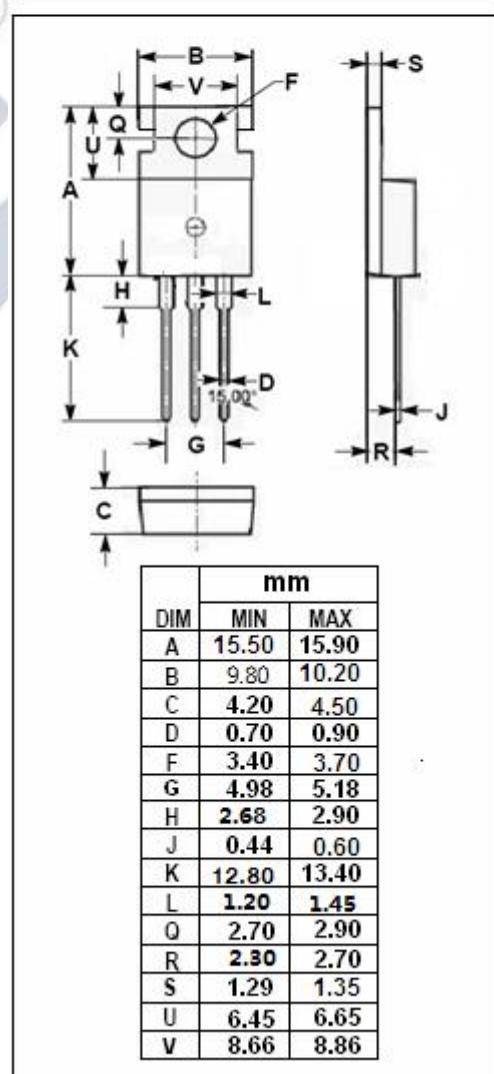
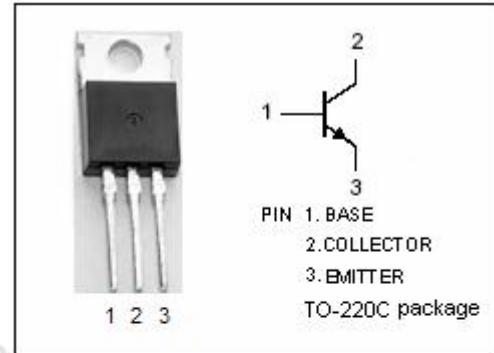
- Designed for use in general purpose amplifier and switching applications.

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

| SYMBOL | PARAMETER | VALUE | UNIT |
|-----------|---|---------|------------------|
| V_{CBO} | Collector-Base Voltage | 100 | V |
| V_{CEO} | Collector-Emitter Voltage | 100 | V |
| V_{EBO} | Emitter-Base Voltage | 5 | V |
| I_C | Collector Current-Continuous | 1 | A |
| I_{CM} | Collector Current-Pulse | 3 | A |
| I_B | Base Current | 0.4 | A |
| P_c | Collector Power Dissipation $T_c=25^\circ\text{C}$ | 30 | W |
| T_j | Junction Temperature | 150 | $^\circ\text{C}$ |
| T_{stg} | Storage Temperature Range | -65~150 | $^\circ\text{C}$ |

THERMAL CHARACTERISTICS

| SYMBOL | PARAMETER | MAX | UNIT |
|--------------|--|------|---------------------------|
| $R_{th j-c}$ | Thermal Resistance,Junction to Case | 4.17 | $^\circ\text{C}/\text{W}$ |
| $R_{th j-a}$ | Thermal Resistance,Junction to Ambient | 62.5 | $^\circ\text{C}/\text{W}$ |



isc Silicon NPN Power Transistors**TIP29C****ELECTRICAL CHARACTERISTICS** $T_c=25^\circ C$ unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | MAX | UNIT |
|----------------------|--------------------------------------|---|-----|-----|------|
| $V_{CEO(sus)}$ | Collector-Emitter Sustaining Voltage | $I_C = 30\text{mA}$; $I_B = 0$ | 100 | | V |
| $V_{CE(\text{sat})}$ | Collector-Emitter Saturation Voltage | $I_C = 1\text{A}$; $I_B = 0.125\text{A}$ | | 0.7 | V |
| $V_{BE(\text{on})}$ | Base-Emitter On Voltage | $I_C = 1\text{A}$; $V_{CE} = 4\text{V}$ | | 1.3 | V |
| I_{CES} | Collector Cutoff Current | $V_{CE} = 100\text{V}$; $V_{EB} = 0$ | | 0.2 | mA |
| I_{CEO} | Collector Cutoff Current | $V_{CE} = 100\text{V}$; $I_B = 0$ | | 0.3 | mA |
| I_{EBO} | Emitter Cutoff Current | $V_{EB} = 5\text{V}$; $I_C = 0$ | | 1.0 | mA |
| h_{FE-1} | DC Current Gain | $I_C = 0.2\text{A}$; $V_{CE} = 4\text{V}$ | 40 | | |
| h_{FE-2} | DC Current Gain | $I_C = 1\text{A}$; $V_{CE} = 4\text{V}$ | 15 | 75 | |
| f_T | Current-Gain—Bandwidth Product | $I_C = 0.2\text{A}$; $V_{CE} = 10\text{V}$; $f = 1\text{MHz}$ | 3 | | MHz |